

TECHNICAL DATA  
DATA SHEET D0122 REV. –

## SILICON SCHOTTKY RECTIFIER DIE

### Ultra Low Reverse Leakage 200°C Operating Temperature

#### Applications:

- Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

#### Features:

- Ultra low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging
- Out Performs 150 Volt Ultrafast Rectifiers

#### Maximum Ratings:

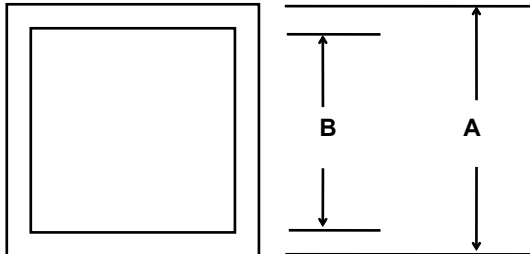
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	150	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form	60	A
Peak One Cycle Non-Repetitive Surge Current	$I_{FSM}$	8.3 ms, Sine pulse <sup>(1)</sup>	860	A
Junction Temperature	$T_J$	-	-55 to +200	°C
Storage Temperature	$T_{stg}$	-	-55 to +200	°C

#### Electrical Characteristics:

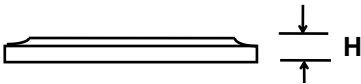
Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop	$V_{F1}$	@ 60 A, Pulse, $T_J = 25\text{ °C}$	0.92	V
	$V_{F2}$	@ 60 A, Pulse, $T_J = 125\text{ °C}$	0.79	V
Reverse Current	$I_{R1}$	@ $V_R = 150\text{V}$ , Pulse, $T_J = 25\text{ °C}$	1.5	mA
	$I_{R2}$	@ $V_R = 150\text{V}$ , Pulse, $T_J = 125\text{ °C}$	24	mA
Junction Capacitance	$C_T$	@ $V_R = 5\text{V}$ , $T_C = 25\text{ °C}$ $f_{SIG} = 1\text{MHz}$ , $V_{SIG} = 50\text{mV (p-p)}$	1500	pF

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**Mechanical Dimensions: In Inches (mm)**



Bottom side metalization Ag-5kA minimum  
 Top side metalization Al -25kA minimum  
 Bottom side is cathode, top side is anode  
 Dimension H =0.0105±0.001(0.27±0.026) (It can be customized according to customer requirements)



A	B
0.200 ± 0.003(5.08 ± 0.08)	0.192 ± 0.003(4.88 ± 0.08)

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